



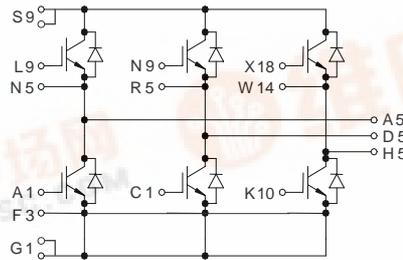
Advanced Technical Information

IGBT Module

Sixpack in ECO-PAC 2

VWI 15-12P1

$I_{C25} = 18 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.3 \text{ V}$



IGBTs		
Symbol	Conditions	Maximum Ratings
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200 V
V_{GES}		± 20 V
I_{C25}	$T_C = 25^{\circ}\text{C}$	18 A
I_{C80}	$T_C = 80^{\circ}\text{C}$	14 A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	20 A
t_{SC} (SCSOA)		$V_{CE} = 720 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive
P_{tot}	$T_C = 25^{\circ}\text{C}$	90 W

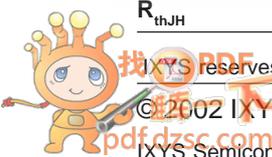
Features

- NPT IGBT's
 - positive temperature coefficient of saturation voltage
 - fast switching
- FRED diodes
 - fast reverse recovery
 - low forward voltage
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated DCB ceramic base plate

Typical Applications

- AC drives
- power supplies with power factor correction

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 10 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.7	V V	
$V_{GE(th)}$	$I_C = 0.4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.8	0.5 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 10 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega$		50 40 290 60 1.2 1.1	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		600	pF
Q_{Gon}		$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 10 \text{ A}$		45	nC
R_{thJC}		(per IGBT)			1.4 K/W
R_{thJH}		(per IGBT) with heatsink compound		2.7	K/W



IXYS reserves the right to change limits, test conditions and dimensions.

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IXYS Semiconductor GmbH
 Edisonstr. 15 D-68623 Lampertheim

www.ixys.net

IXYS Corporation
 3540 Bassett Street, Santa Clara, CA, 95054

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	15	A
I_{F80}	$T_C = 80^\circ\text{C}$	10	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 10\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.6 1.9	V V
I_{RM} t_{rr}	$I_F = 10\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$		13 110	A ns
R_{thJC} R_{thJH}	(per diode) (per diode) with heatsink compound		5.0	3.5 K/W K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}; t = 1\text{ s}$	3600	V~
M_d	mounting torque (M4)	1.5 - 2.0	Nm lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight			24	g

Dimensions in mm (1 mm = 0.0394")
